

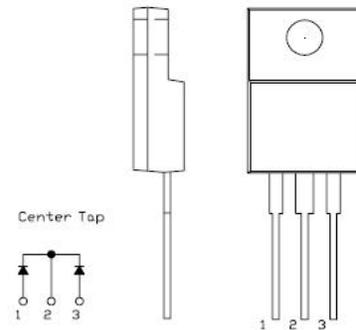
## MURF1020CT ULTRAFAST RECTIFIER

### Applications:

- Switching Power Supply
- Power Switching Circuits
- General Purpose

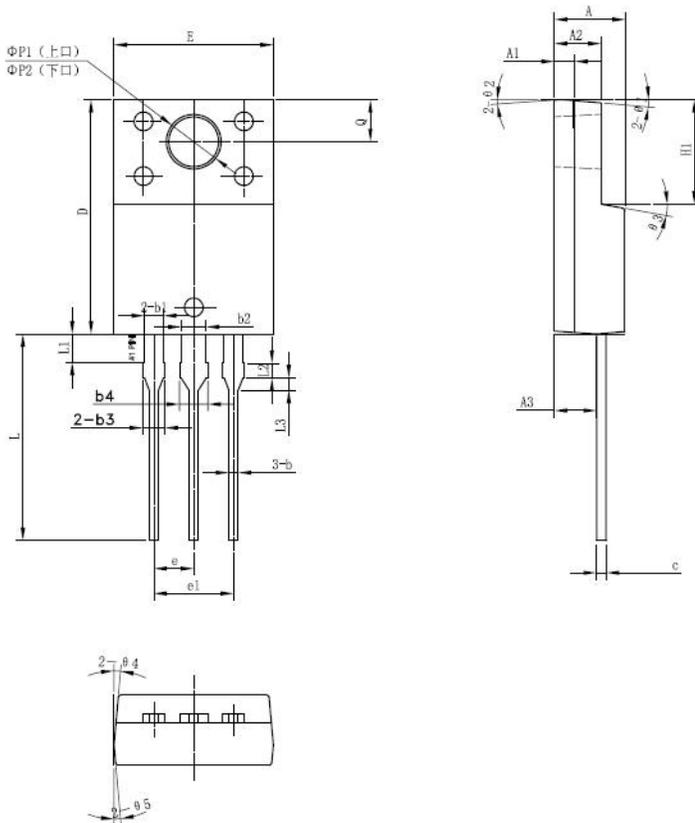
### Features:

- Ultra-Fast Switching
- High Current Capability
- Low Reverse Leakage Current
- High Surge Current Capability
- Plastic Material has UL Flammability Classification 94V-0
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



OUTLINE DRAWING

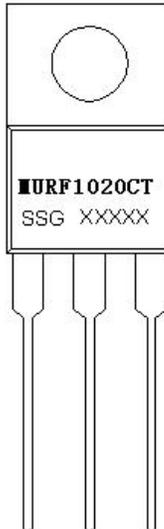
### Mechanical Dimensions: In mm



SYMBOL	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
c	0.55	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上口)	3.30	3.50	3.70
ΦP2(下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

### ITO-220AB

**Marking Diagram:**



Where XXXXX is YYWWL

MUR = Device Type  
 F = Package type  
 10 = Forward Current (10A)  
 20 = Reverse Voltage (200V)  
 CT = Configuration  
 SSG = SSG  
 YY = Year  
 WW = Week  
 L = Lot Number

**Cautions:** Molding resin  
 Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
MURF1020CT	ITO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	$V_{RRM}$	-	200	V
Working Peak Reverse Voltage	$V_{RWM}$			
DC Blocking Voltage	$V_R$			
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_c=100^\circ\text{C}$ , rectangular wave form	10	A
Peak One Cycle Non-Repetitive Surge Current (Per leg)	$I_{FSM}$	8.3ms, Half Sine pulse	100	A

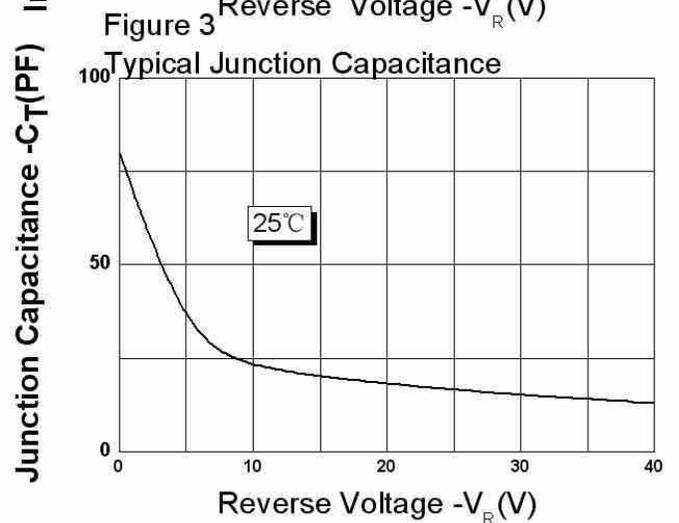
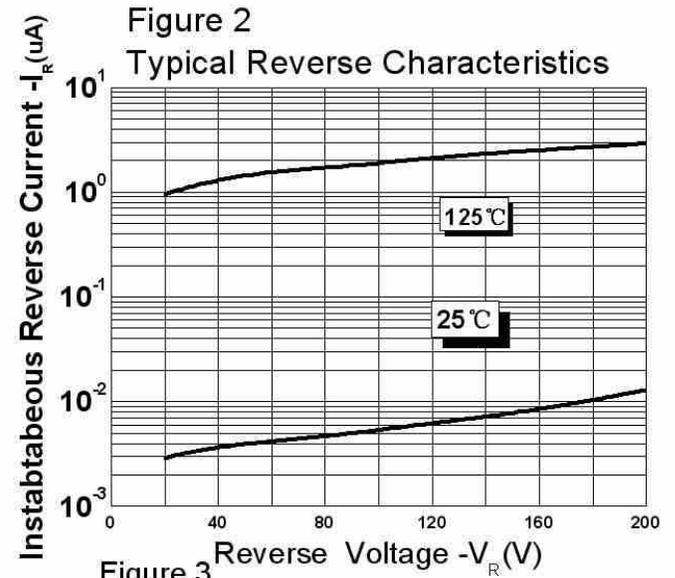
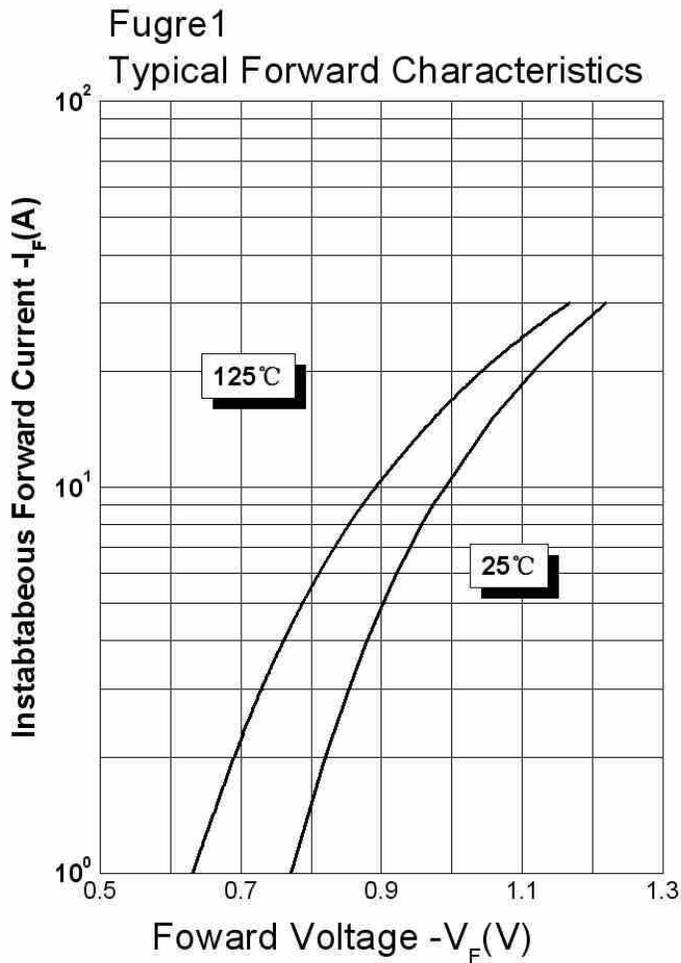
**Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop (Per leg)*	V <sub>F1</sub>	@ 10A, Pulse, T <sub>J</sub> = 25°C	1.2	V
	V <sub>F2</sub>	@ 10A, Pulse, T <sub>J</sub> = 100°C	1.0	V
Reverse Current(Per leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25°C	10	μA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 100°C	100	μA
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =500mA, I <sub>R</sub> =1A, and I <sub>rm</sub> =250mA	35	ns
RSM Isolation Voltage (t=1.0 second, R.H.< =30%, T <sub>A</sub> =25°C)	V <sub>iso</sub>	Clip mouting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	4500	V
		Clip mouting, the epoxy body is inside the heatsink	3500	
		Screw mounting, the epoxy body is inside the heatsink	1500	

\* Pulse width < 300 μs, duty cycle < 2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T <sub>J</sub>	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>θJC</sub>	DC operation	5.0	°C/W
Approximate Weight	wt	-	2.0	g
Case Style	ITO-220AB			



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